

< C band internally matched power GaAs FET >

MGFC42V3436

3.4 – 3.6 GHz BAND / 16W

DESCRIPTION

The MGFC42V3436 is an internally impedance-matched GaAs power FET especially designed for use in 3.4 – 3.6 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

- High output power
P1dB=16W (TYP.) @f=3.4 – 3.6GHz
- High power gain
GLP=14dB (TYP.) @f=3.4 – 3.6GHz
- High power added efficiency
P.A.E.=37% (TYP.) @f=3.4 – 3.6GHz
- Low distortion [item -51]
IM3=-45dBc (TYP.) @Po=32dBm S.C.L

APPLICATION

- item 01 : 3.4 – 3.6 GHz band power amplifier
- item 51 : 3.4 – 3.6 GHz band digital radio communication

QUALITY

- IG

RECOMMENDED BIAS CONDITIONS

- VDS=10V • ID=4.5A • RG=25ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	15	A
IGR	Reverse gate current	-40	mA
IGF	Forward gate current	84	mA
PT *1	Total power dissipation	78.9	W
Tch	Channel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C

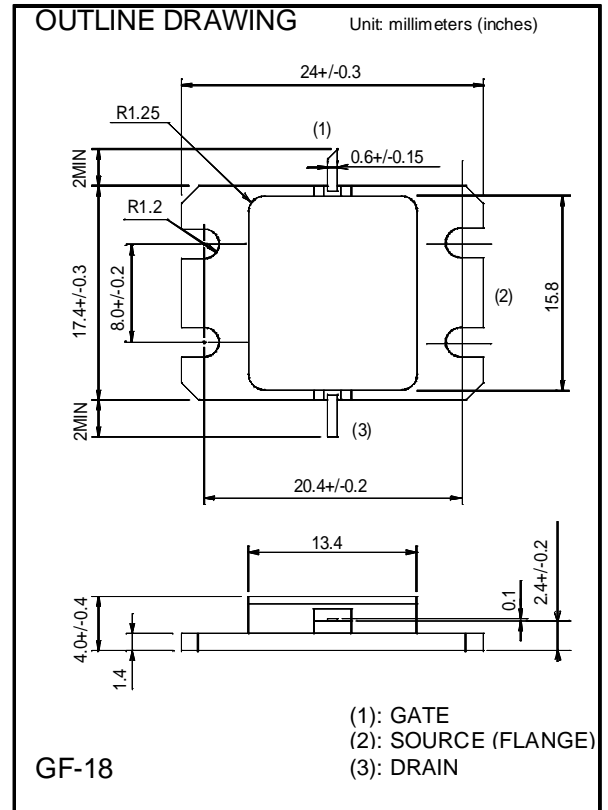
*1 : Tc=25°C

Electrical characteristics (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	11	-	A
gm	Transconductance	VDS=3V, ID=4.4A	-	4	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=80mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=4.5A f=3.4 – 3.6GHz	41.5	42.5	-	dBm
GLP	Linear Power Gain		12	14	-	dB
ID	Drain current		-	4.5	-	A
P.A.E.	Power added efficiency		-	37	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance		delta Vf method	-	-	1.9

*2 : item -51 , 2 tone test, Po=32dBm Single Carrier Level , f=3.6GHz, delta f=5MHz

*3 : Channel-case



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